

Abstract of the Disclosure

The method of forming a ferroelectric memory device includes forming capacitor patterns over a substrate, each capacitor pattern having an adhesive assistant pattern, a lower electrode, a ferroelectric pattern, and an upper electrode. An oxygen barrier layer is formed over the substrate and is etched

5 to expose a sidewall of the ferroelectric pattern but not a sidewall of the adhesive assistant pattern. Then, a thermal process for curing ferroelectricity of the ferroelectric pattern is performed.